



2N5088 (3DG5088)

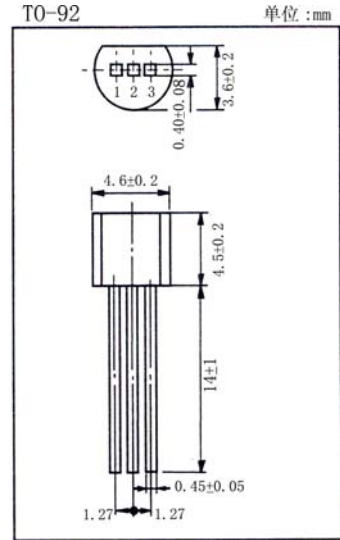
硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途：用于集电极电流在 1uA~50uA 的低噪声、高增益的一般放大电路。

Purpose: This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from 1 μ A to 50 μ A.

极限参数/Absolute maximum ratings(Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	35	V
V _{CE0}	30	V
V _{EB0}	4.5	V
I _C	100	mA
P _C	625	mW
T _j	150	°C
T _{stg}	-55~150	°C



引脚：1. E 2. B 3. C

电性能参数/Electrical characteristics(Ta=25°C)

参数符号 Symbol	测试条件 Test condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
I _{CB0}	V _{CB} =20V	I _E =0			50	nA
I _{EB0}	V _{EB} =3V	I _C =0			50	nA
h _{FE(1)}	V _{CE} =5V	I _C =100 μ A	300	900		
h _{FE(2)}	V _{CE} =5V	I _C =10mA	300			
h _{FE(3)}	V _{CE} =5V	I _C =1mA	350			
V _{CE(sat)}	I _C =10mA	I _B =1mA			0.5	V
V _{BE(on)}	I _C =10mA	V _{CE} =5V			0.8	V
V _{CE0}	I _C =1mA	I _B =0	30			V
V _{CB0}	I _C =100 μ A	I _E =0	35			V
f _T	I _C =500 μ A	V _{CE} =5mA	f=20MHz			MHz
C _{cb}	V _{CB} =5V	I _E =0	f=100KHz		4	pF
C _{eb}	V _{BE} =0.5V	I _C =0	f=100KHz		10	pF



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